PATENT APPLICATION

RESPONSE UNDER 37 CFR §1.116 EXPEDITED PROCEDURE TECHNOLOGY CENTER ART UNIT 1763

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of

Kazuo ICHIKAWA et al.

Application No.: 09/670,877

Filed: September 27, 2000

For: CVD SUBSTRATE AND CLEANING METHOD

Group Art Unit: 1763

Examiner: R. Zerviger

Docket No.: 107469

R §1.11**6**5

AMENDMENT AFTER FINAL REJECTION UNDER 37 CFR §1.116

Director of the U.S. Patent and Trademark Office Washington, D.C. 20231

Sir:

In reply to the August 6, 2002 Office Action, please amend the above-identified application as follows:

IN THE CLAIMS:

Please replace claims 1 and 3 as follows:

1. (Amended) A CVD system provided with a plasma generator having a plasma generation chamber separated from a film deposition chamber in which a substrate is arranged, wherein a material gas is directly supplied into the film deposition chamber, radicals in the plasma are introduced into the film deposition chamber from the plasma generator through introduction holes of a lower plate, and a thin film is deposited on the substrate, said CVD system further comprising:

a cleaning gas feeder provided to said plasma generator, said lower plate is connected to ground, and

